

**Appl. No. 09/643,004**

less than about 645 °C and less than about 500 milliTorr or perhaps different ranges, as determinable by those skilled in the art, depending on above mentioned factors. In such a process regime, pressure might bear a more significant effect on selectivity compared to temperature. The unconventional CVD process regime may be conducive to forming a deposition layer only about 1 to 5 atoms or molecules thick. Accordingly, by using a nucleation layer in keeping with the various aspects of the present invention, unconventional CVD may also be used to form a deposition layer. --

### In the Claims

**Please cancel claims 1-8 and 42-46 without prejudice.**